BC212, BC212B, BC213, BC214

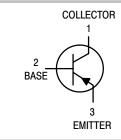
Amplifier Transistors

PNP Silicon



ON Semiconductor[™]

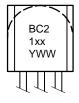
http://onsemi.com





CASE 29 STYLE 17

MARKING DIAGRAMS



ORDERING INFORMATION

Device	Package	Shipping
BC212	TO-92	5000 Units/Box
BC212B	TO-92	5000 Units/Box
BC212BRL1	TO-92	2000/Tape & Reel
BC212BZL1	TO-92	2000/Ammo Pack
BC213	TO-92	5000 Units/Box
BC214	TO-92	5000 Units/Box
BC214RL1	TO-92	2000/Tape & Reel

MAXIMUM RATINGS

			1
Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC212 BC213 BC214	V _{CEO}	-50 -30 -30	Vdc
Collector-Base Voltage BC212 BC213 BC214	V _{CBO}	-60 -45 -45	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ι _C	-100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ extsf{ heta}JC}$	125	°C/W

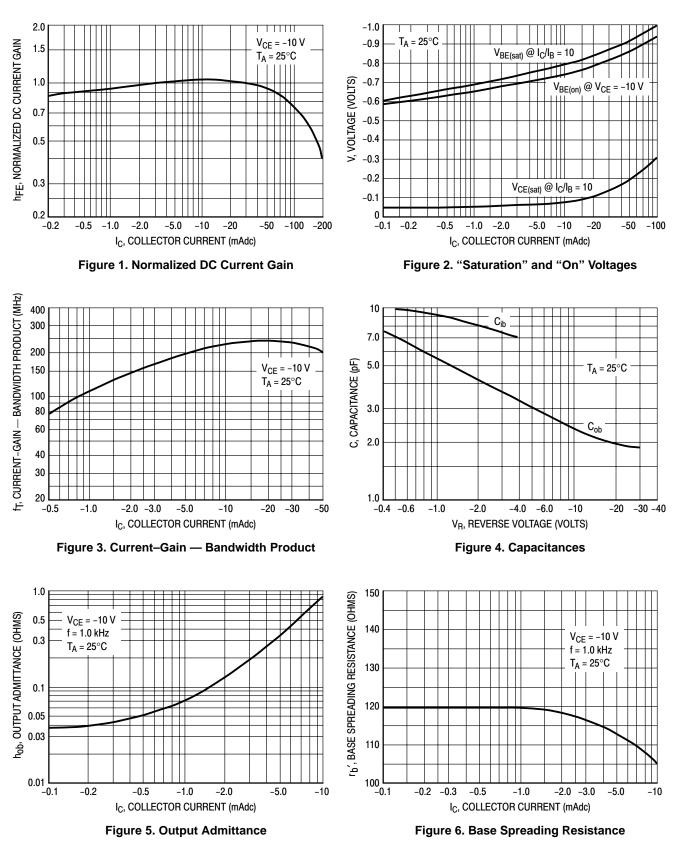
BC212, BC212B, BC213, BC214

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Collector–Emitter Breakdown Voltage ($I_C = -2.0 \text{ mAdc}, I_B = 0$)	BC212 BC213 BC214	V _{(BR)CEO}	50 30 30	_ _ _	_ _ _	Vdc
Collector–Base Breakdown Voltage ($I_C = -10 \ \mu A, I_E = 0$)	BC212 BC213 BC214	V _{(BR)CBO}	60 45 45		- - -	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10 \ \mu Adc, I_C = 0$)	BC212 BC213 BC214	V _{(BR)EBO}	-5 -5 -5	- - -	_ _ _	Vdc
Collector–Emitter Leakage Current $(V_{CB} = -30 \text{ V})$	BC212 BC213 BC214	I _{CBO}	- - -	- - -	-15 -15 -15	nAdc
Emitter–Base Leakage Current $(V_{EB} = -4.0 \text{ V}, I_C = 0)$	BC212 BC213 BC214	I _{EBO}	- - -	- - -	-15 -15 -15	nAdc
ON CHARACTERISTICS						
DC Current Gain (I _C = -10μ Adc, V _{CE} = -5.0 Vdc)	BC212 BC213 BC214	h _{FE}	40 40 100	- - -		_
$(I_{C} = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	BC212 BC213 BC214		60 80 140	- - -	_ _ 600	
$(I_{C} = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$ (Note 1.)	BC212, BC214 BC213			120 140		
Collector–Emitter Saturation Voltage ($I_C = -10$ mAdc, $I_B = -0.5$ mAdc) ($I_C = -100$ mAdc, $I_B = -5.0$ mAdc) (Note 1.)		V _{CE(sat)}		-0.10 -0.25	_ _0.6	Vdc
Base–Emitter Saturation Voltage ($I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}$)		V _{BE(sat)}	-	-1.0	-1.4	Vdc
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}$)		V _{BE(on)}	-0.6	-0.62	-0.72	Vdc
DYNAMIC CHARACTERISTICS				•		•
Current–Gain – Bandwidth Product ($I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc, f = 100 MHz)	BC212 BC214 BC213	fT	_ _ _	280 320 360	_ _ _	MHz
Common–Base Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz})$		C _{ob}	_	_	6.0	pF
Noise Figure $(I_C = -0.2 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz})$ $(I_C = -0.2 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz}, f = 200 \text{ Hz})$	BC214 BC212, BC213	NF		-	2 10	dB
Small–Signal Current Gain ($I_C = -2.0$ mAdc, $V_{CE} = -5.0$ Vdc, f = 1.0 kHz)	BC212 BC213 BC214 BC212B	h _{fe}	60 80 140 200	- - - -	- - - 400	-

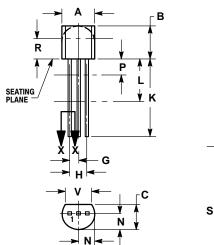
1. Pulse Test: Tp 300 s, Duty Cycle 2.0%.

BC212, BC212B, BC213, BC214



PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R 2. 3. IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND

4 BEYOND DIMENSION K MINIMUM

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER

are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes ON Semiconductor and ON Semiconductor and a retrademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: ONlit@hibbertco.com Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor - European Support

- German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET) Email: ONlit-german@hibbertco.com Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET) French
- Email: ONlit-french@hibbertco.com
- English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT) Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781 *Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST) Email: ONlit-spanish@hibbertco.com Toll-Free from Mexico: Dial 01-800-288-2872 for Access -

then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor - Asia Support Phone: 303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time) Toll Free from Hong Kong & Singapore: 001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031 Phone: 81-3-5740-2700 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.